

---

# 1Gbps Rail to Rail LVDS receiver

---

## SPECIFICATION

### 1 FEATURES

- iHP SiGe BiCMOS 0.13 um
- 3.3 V power supply
- 1 Gbps (DDR MODE) switching rates
- Conforms to TIA/EIA-644 LVDS standards without hysteresis
- Rail to rail input range
- Temperature range: -40 °C to + 85 °C
- Optimized for pad-limited layout design
- Portable to other technologies (upon request)

### 2 APPLICATION

- Point-to-point data receiver
- Multidrop buses
- Clock distribution
- Backplane receiver
- Backplane data receiver
- Cable data receiver

### 3 OVERVIEW

The LVDS receiver converts LVDS data to CMOS data stream. It could receive data or clock signals with rate up to 1Gbps DDR MODE. The LVDS receiver has rail to rail input range and corresponds to TIA/EIA-644 LVDS standards without hysteresis. There is also embedded terminator which can be enabled/disabled by the control pin (EN\_RES).

The LVDS receiver is designed on TSMC SiGe BiCMOS 0.13 um technology.

## 4 STRUCTURE

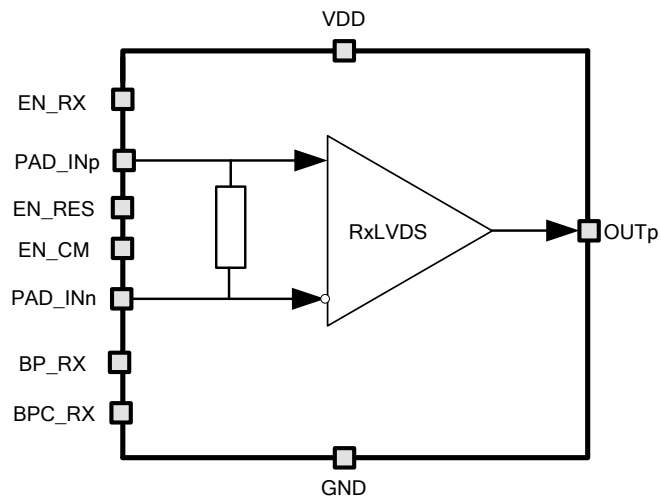


Figure 1: Rail to rail LVDS receiver 1 Gbps structure.

## 5 PIN DESCRIPTION

Name	Direction	Description
EN_CM	I	Input common-mode voltage enable
EN_RES	I	On-chip resistor enable
EN_RX	I	LVDS receiver enable
PAD_INp	I	Input differential LVDS signal
PAD_INn		
OUTp	O	Output CMOS signal
BP_RX	I	Voltage reference from bias
BPC_RX		
VDD	IO	Supply voltage 3.3 V
GND	IO	Ground

Table 1: LVDS receiver truth table.

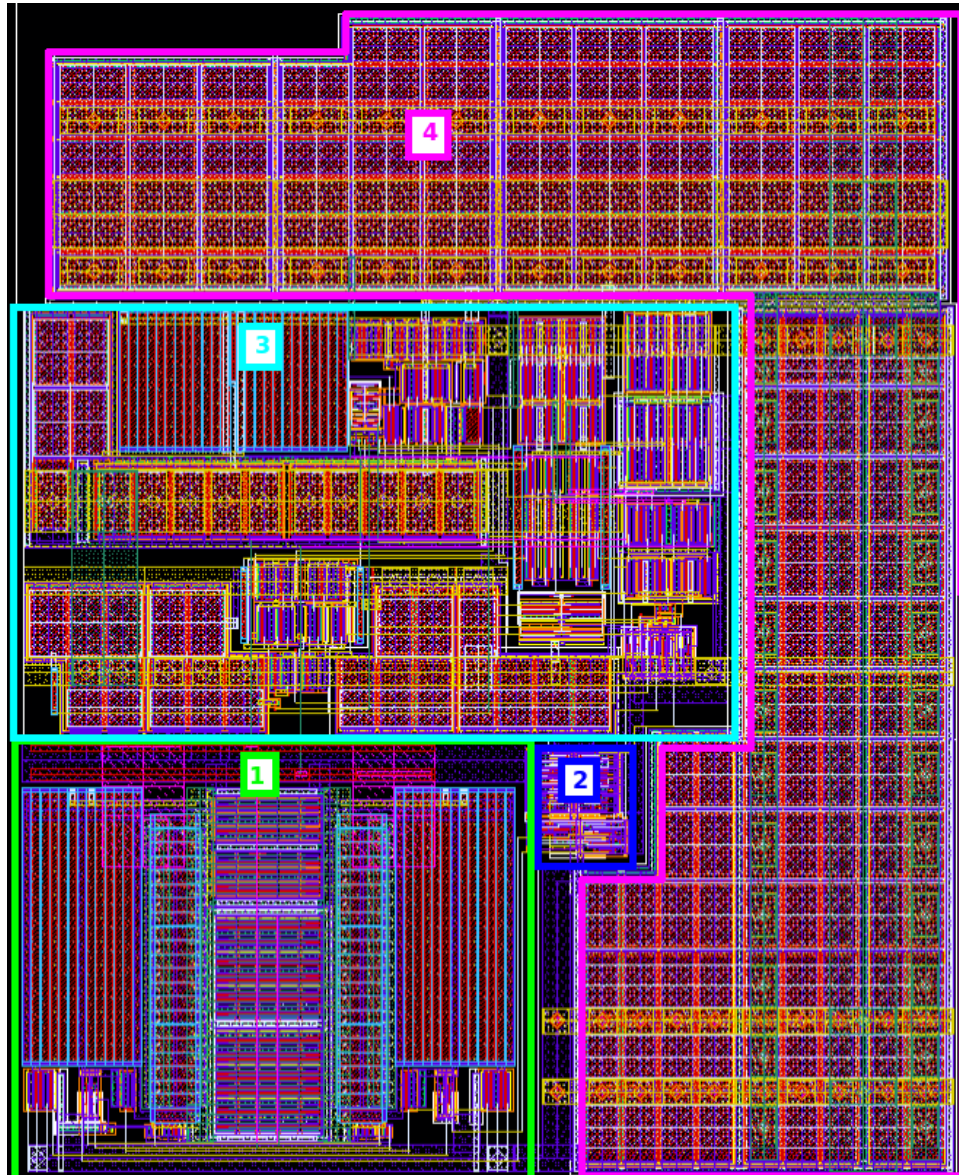
Mode	Input			Output
	EN_RX	PAD_INp	PAD_INn	OUTp
Receive	1	1	0	1
		0	1	0
Power down	0	X	X	0

## 6 LAYOUT DESCRIPTION

Rail to Rail LVDS Receiver dimensions are given in the table 2.

**Table 2:** Block dimension.

Dimension	Value	Unit
Height	170	um
Width	140	um



**Figure 2:** Rail to rail LVDS Receiver layout view.

1. On-chip 100 ohm resistor
2. Digital buffer
3. Rail to rail LVDS receiver
4. MOS capacitors

## 7 OPERATING CHARACTERISRICS

### 7.1 TECHNICAL CHARACTERISTICS

Technology \_\_\_\_\_ SiGe BiCMOS 0.13um  
 Status \_\_\_\_\_ pre-silicon verification  
 Area \_\_\_\_\_ 0.023 mm<sup>2</sup>

### 7.2 ELECTRICAL CHARACTERISTICS

The values of electrical characteristics are special for  $V_{dd} = 2.7 \div 3.6$  V,  $T = -40 \div +85$  °C. Typical value are at  $V_{dd} = 3.3$ V,  $T = +85$  °C, unless otherwise specified.

Parameter	Symbol	Condition	Value			Unit
			min	typ	max	
Supply analog voltage	$V_{dd}$	-	2.7	3.3	3.6	V
Operating temperature range	T	-	-40	27	+85	°C
Input voltage range (common-mode)	$V_{in}$	-	0	1.2	3.3	V
Input differential threshold	$V_{th}$	-	-		100	mV
Receiver differential input impedance	$R_{in}$	-	90	107	130	$\Omega$
DC power current from $V_{dd}$	$I_{VDD}$	-	0.89	0.97	1.1	mA
Total DC power	W	-	2.4	3.2	3.96	mW
Stand-by current	$I_{st}$	-	1	1.5	11	nA
Output voltage range	$V_{out}$	-	0	-	3.3	V
Differential time propagation delay, high to low	$t_{PHLDT}$	-	0.77	1.1	1.7	ns
Differential time propagation delay, low to high	$t_{PLHDT}$	-	0.77	1.1	1.7	ns
AC power current from $V_{dd}$	$I_{VDD}$	-	1.25	1.47	1.66	mA
Total AC power	W	-	3.4	4.85	6	mW
Clock jitter, rms	$t_{RJ}$	$C_L = 100$ f	1.1	1.9	2.4	ps
Clock jitter, max (p-p)	$t_{DJM}$		5.4	10.8	12	ps
Data jitter, deterministic	$t_{DJ}$		2.7	11	17	ps
Input voltage high level	$V_{IH}$	For digital inputs	$0.8 V_{dd}$	-	$V_{dd}$	V
Input voltage low level	$V_{IL}$		0	-	$0.2 V_{dd}$	V

## 8 DELIVERABLES

IP contents:

- Schematic or NetList
- Layout or blackbox
- Extracted view (optional)
- GDSII
- DRC, LVS, antenna report
- Test bench with saved configurations (optional)
- Documentation

## REVISION HISTORY

From version 1.1:

- Section 1
- Section 3
- Subsection 7.2 update